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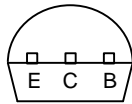
2SC2001

NPN Silicon Plastic-Encapsulate Transistor

Features

- Capable of 0.6Watts of Power Dissipation.
- Collector-current 0.7A
- Collector-base Voltage 30V
- Operating and storage junction temperature range: -55°C to +150°C

Pin Configuration
Bottom View



Electrical Characteristics @ 25°C Unless Otherwise Specified

Symbol	Parameter	Min	Max	Units
OFF CHARACTERISTICS				
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage ($I_C=10\text{mAdc}$, $I_B=0$)	25	---	Vdc
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage ($I_C=100\mu\text{Adc}$, $I_E=0$)	30	---	Vdc
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage ($I_E=100\mu\text{Adc}$, $I_C=0$)	5.0	---	Adc
I_{CBO}	Collector Cutoff Current ($V_{CB}=30\text{Vdc}$, $I_E=0$)	---	0.1	μAdc
I_{CEO}	Collector Cutoff Current ($V_{CE}=20\text{Vdc}$, $I_E=0$)	---	0.1	Vdc
I_{EBO}	Emitter Cutoff Current ($V_{EB}=5.0\text{Vdc}$, $I_C=0$)	---	0.1	μAdc

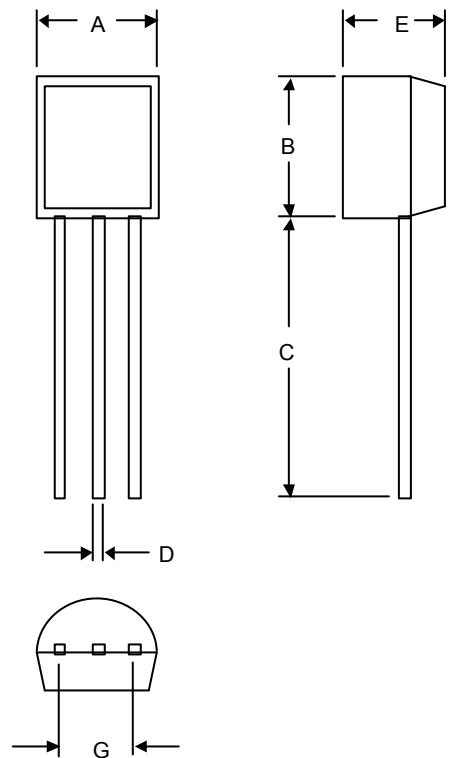
ON CHARACTERISTICS

h_{FE}	DC Current Gain ($I_C=100\text{mAdc}$, $V_{CE}=1.0\text{Vdc}$)	90	400	---
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage ($I_C=700\text{mAdc}$, $I_B=70\text{mAdc}$)	---	0.6	Vdc
$V_{(BE)sat}$	Base-Emitter Saturation Voltage ($I_C=700\text{mAdc}$, $I_B=70\text{mAdc}$)	---	1.2	Vdc
fT	Transition Frequency ($V_{CE}=6.0\text{Vdc}$, $I_C=10\text{mAdc}$, $f=30\text{MHz}$)	50	---	MHz

CLASSIFICATION OF h_{FE}

Rank	M	L	K
Range	90-180	135-270	200-400

TO-92



DIMENSIONS

DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.170	.190	4.33	4.83	
B	.170	.190	4.30	4.83	
C	.550	.590	13.97	14.97	
D	.010	.020	0.36	0.56	
E	.130	.160	3.30	3.96	
G	.010	.104	2.44	2.64	